

L Number	Hits	Search Text	DB	Time stamp
-	739	cmos and spacer and implant\$6 and metalization	USPAT	2001/04/24 14:32
-	739	cmos and spacer and implant\$6 and metalization	USPAT	2001/04/23 14:57
-	690	cmos and spacer and implant\$6 and metalization and mask\$4	USPAT	2001/04/23 14:58
-	16	dose near5 surface adj concentration	USPAT	2001/04/24 14:33
-	292	mdd	USPAT	2001/04/24 15:23
-	1237	low adj energy near10 high adj energy	USPAT	2001/04/24 15:26
-	36	low adj energy near10 high adj dose and semiconductor	USPAT	2001/04/24 15:42
-	140	plasma adj immersion	USPAT	2003/02/27 13:48
-	67	(plasma adj immersion) and kev	USPAT	2001/04/24 15:56
-	41	dose near10 surface adj concentration	USPAT	2001/04/24 15:57
-	4454	"1.times.10.sup.20" or "1.times.10.sup.18" or "1.times.10.sup.19"	USPAT	2001/04/25 09:32
-	3807	"1.times.10.sup.20" or "1.times.10.sup.18" or "1.times.10.sup.19" and dos\$3	USPAT	2001/04/25 09:39
-	3565	"1.times.10.sup.20" or "1.times.10.sup.18" or "1.times.10.sup.19" near10 (dose\$1 or dosag\$2)	USPAT	2001/04/25 09:39
-	3547	"1.times.10.sup.20" or "1.times.10.sup.18" or "1.times.10.sup.19" near10 (dose\$1 or dosag\$2) same implant\$3 same source	USPAT	2001/04/25 09:40
-	24	,"1.times.10.sup.20" or "1.times.10.sup.18" or "1.times.10.sup.19") near10 (dose\$1 or dosag\$2) same implant\$3 same source	USPAT	2001/04/25 13:10
-	50	dummy adj gate near5 implant\$6	USPAT	2001/04/25 10:51
-	0	("1.times.10.sup.20" or "1.times.10.sup.18" or "1.times.10.sup.19") near10 (dose\$1 or dosag\$2) same implant\$3 same source	EPO; JPO	2001/04/25 13:10
-	232	(dose\$1 or dosag\$2) same implant\$3 same source	EPO; JPO	2001/04/25 13:10
-	0	(dose\$1 or dosag\$2) same implant\$3 same source and plasma and immersion	EPO; JPO	2001/04/25 13:11
-	0	(dose\$1 or dosag\$2) same source and plasma and immersion	EPO; JPO	2001/04/25 13:11
-	7	source and plasma and immersion	EPO; JPO	2001/04/25 13:11
-	122	plasma near2 immersion and kev	USPAT	2003/02/27 14:05